

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 118988		APPLICATION NO. New U.S. Application 10/797,201	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Jun HATAKEYAMA et al.			
				FILING DATE March 11, 2004		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
	1.	US 6,420,088 B1	7/16/2002	ANGELOPOULOS et al.			
	2.	5,294,680	3/15/1994	KNORS et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
R.A.	3.	JP A 10-69072 w/abstract & transl.	3/10/1998	JAPAN			
	4.	JP B2 7-69611 w/abstract & transl.	7/31/1995	JAPAN			
R.A.	5.	JP A 6-118631 w/abstract & transl.	4/28/1994	JAPAN			
R.A.	6.	JP A 6-118656 w/abstract & transl.	4/28/1994	JAPAN			
RA	7.	JP A 8-87115 w/abstract & transl.	4/2/1996	JAPAN			
RA	8.	JP A 8-179509 w/abstract & transl.	7/12/1996	JAPAN			
	9.	JP B2 3287119 w/abstract & transl.	3/15/2002	JAPAN			
	10.	JP B2 3118887 w/abstract & transl.	10/13/2000	JAPAN			
KA.	11.	JP A 2000-356854 w/abstract & transl.	12/26/2000	JAPAN			
RA.	12.	JP A 5-27444 w/abstract & transl.	2/5/1993	JAPAN			
RA.	13.	JP A 11-60735 w/abstract & transl.	3/5/1999	JAPAN			
K.A.	14.	JP A 6-138664 w/abstract & transl.	5/20/1994	JAPAN			
RA.	15.	JP A 2001-53068 w/abstract & transl.	2/23/2001	JAPAN			
RA.	16.	JP A 2001-92122 w/abstract & transl.	4/6/2001	JAPAN			
RA.	17.	JP A 2001-343752 w/abstract & transl.	12/14/2001	JAPAN			
RA.	18.	JP A 57-83563 w/abstract	5/25/1982	JAPAN			
RA.	19.	JP A 57-131250 w/abstract	8/14/1982	JAPAN			
RA.	20.	JP A 56-129261 w/abstract	10/9/1981	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
RA.	21.	Won D. Kim et al.; "Investigation of Hardmask/BARC Materials for 157nm Lithography"; In Microlithographic Techniques in Integrated Circuit Fabrication II, Chris A. Mack, Xiacong Yuan, Editors, Proceedings of SPIE; Vol. 4226; 2000; pp 93-106					

Date: March 11, 2004

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CA	22.	Tom Lynch et al.; "Properties and Performance of Near UV Reflectivity Control Layers"; SPIE; Vol. 2195; pp 225-229
P.A.	23.	Qinghuang Lin et al.; "A High Resolution 248 nm Bilayer Resist"; Part of SPIE Conference of Advances in Resist Technology and Processing XVI, Santa Clara, California; March 1999; SPIE; Vol. 3678; pp 241-250
P.A.	24.	Peter Trefonas et al.; "Organic Antireflective Coatings for 193nm Lithography"; Part of SPIE Conference of Advances in Resist Technology and Processing XVI, Santa Clara, California; March 1999; SPIE; Vol. 3678; pp 702-712
EXAMINER R. Ashton	DATE CONSIDERED 9-6-05	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

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Sheet 1 of 2

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Date: April 14, 2004